

FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP
(Rev. 5/92) 225 Franklin Street, Boston, MA 02110
Telephone: (617) 426-9180

MIT.9944
ATTORNEY DOCKET NO.

10/632,442
SERIAL NO.

APPLICANT: McGill et al.

GROUP: ~~Unknown~~

FILING DATE: August 1, 2003

EXAMINER: ~~Unknown~~

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
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	AG						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AH						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AI	"Metalorganic Vapor Phase Epitaxy Growth and Characterization of $(Al_xGa_{1-x})_{0.5}In_{0.5}P/Ga_{0.5}In_{0.5}P$ ($x=0.4$, 0.7 , and 1.0) Quantum Wells on 15° -Off-(100) GaAs Substrates at High Growth Rate" Jou et al. <i>Jpn. Journal of Applied Physics</i> . October 1993. Vol. 32, No. 10.
	AJ	
	AK	
	AL	
	AM	
	AN	

EXAMINER

DATE CONSIDERED

6/05

EXAMINER:

Initial if citation considered, with or without citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Unknown-10/632,442
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GROUP: Unknown

2815
EXAMINER: Unknown

JACKSON

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	6,064,076	05/16/2000	Chen et al.			05/20/1998
	AB	5,751,753	05/12/1998	Uchida			07/23/1996
	AC	6,433,364	08/13/2002	Hosoba et al.			03/29/2001
	AD	6,081,540	06/27/2000	Nakatsu			12/18/1997
	AE	5,300,794	04/05/1994	Melman et al.			03/19/1991
	AF	5,363,392	11/08/1994	Kasukawa et al.			11/18/1992
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AI	"Growth and Characterization of InGaP Yellow-Green Light-Emitting Diodes by Liquid-Phase Epitaxy," Chen et al. <i>Japanese Journal of Applied Physics</i> . January 1992. Vol. 31.
	AJ	"High-Efficiency InGaP Light-Emitting Diodes on GaP Substrates," Stinson et al. <i>Applied Physics Letters</i> . May 1991. Vol. 58, No. 18.
	AK	"AlGaInP/GaInP Double-Heterostructure Orange Light-Emitting Diodes on GaAsP Substrates Prepared by Metalorganic Vapor-Phase Epitaxy," Lin et al. <i>Journal of Crystal Growth</i> . 1994. Vol. 137.
	AL	"Metalorganic Vapor Phase Epitaxy Growth and Characterization of $(\text{Al}_x\text{Ga}_{1-x})_{0.5}\text{In}_{0.5}\text{P}/\text{Ga}_{0.5}\text{In}_{0.5}\text{P}$ ($x=0.4, 0.7, \text{ and } 1.0$) Quantum Wells on 15° -Off-(100) GaAs Substrates at High Growth Rate," Jou et al. <i>Japanese Journal of Applied Physics</i> . October 1993. Vol. 32, No. 10.
	AM	"Yellow-Green Emission for ETS-LEDs and lasers based on a strained-InGaP quantum well heterostructure grown on a transparent, compositionally graded AlInGaP buffer," McGill et al. <i>Mat. Res. Symp. Proc.</i> 2003. Vol. 744
	AN	"Growth and Characterization of Lattice-Mismatched In _{1-x} Ga _x P Yellow Light Emitting Diodes on GaP," Paul Liu, Phd. Thesis, University of Illinois. 1997.

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EXAMINER INITIAL		
	AI	"Gas-Source Molecular Beam Epitaxial Growth, Characterization, and Light-Emitting diode application of $\text{In}_x\text{Ga}_{1-x}\text{P}$ on GaP(100)," Chin et al. <i>Applied Physics Letters</i> . May 1993. Vol. 62, No. 19.
	AJ	"Highly Strained $\text{In}_x\text{Ga}_{1-x}\text{P}$ /GaP Quantum Wells Grown on GaP and on an $\text{In}_{x/2}\text{Ga}_{1-x/2}\text{P}$ Buffer Layer by Gas-Source Molecular Beam Epitaxy," Bi et al. <i>Journal of Crystal Growth</i> . 1996. Vol. 165.
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	AA	2001/0028061	10/11/2001	Hosoba et al.			03/29/2001
	AB	6,108,360	08/22/2000	Razeghi			06/06/1997
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EXAMINER INITIAL		
	AJ	"Evolution of microstructure and dislocation dynamics in $\text{In}_{0.5}\text{Ga}_{0.5}\text{P}$ graded Buffers grown on GaP by metalorganic vapor phase epitaxy: engineering device-quality substrate materials," Kim et al. <i>J. Vac. Sci. Technol. B</i> . Jul/Aug 1999. Vol. 17.
	AJ	"Yellow-Green emission for ETS-LEDs and Lasers based on a strained InGaP quantum well heterostructure grown on a transparent, compositionally graded AlInGaP buffer," McGill et al. <i>Mat. Res. Soc. Symp.</i> 2003: Vol. 744.
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